N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.0055 at V_{GS} = 10 V	20
	0.009 at V_{GS} = 4.5 V	16

FEATURES

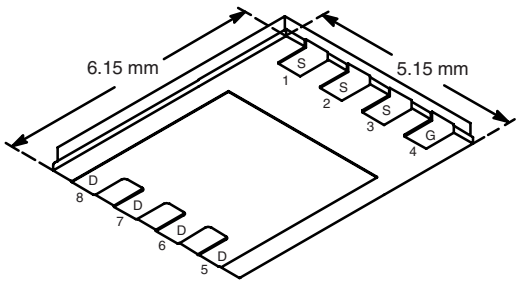
- **Halogen-free available**
- TrenchFET® Power MOSFET
- Q_g Optimized

RoHS COMPLIANT

APPLICATIONS

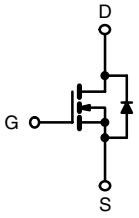
- Synchronous Rectifier for DC/DC

PowerPAK® SO-8



Bottom View

Ordering Information: Si7366DP-T1-E3 (Lead (Pb)-free)
Si7366DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**10 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	20	13	A
	T_A = 70 °C		17	10	
Pulsed Drain Current (10 µs Pulse Width)		I_{DM}	50		
Continuous Source Current (Diode Conduction)[a]		I_S	4.1	1.4	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	5	1.7	W
	T_A = 70 °C		3.2	1.1	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature)[b,c]			260		

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	20	25	°C/W
	Steady State		53	70	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	3.4	4.5	

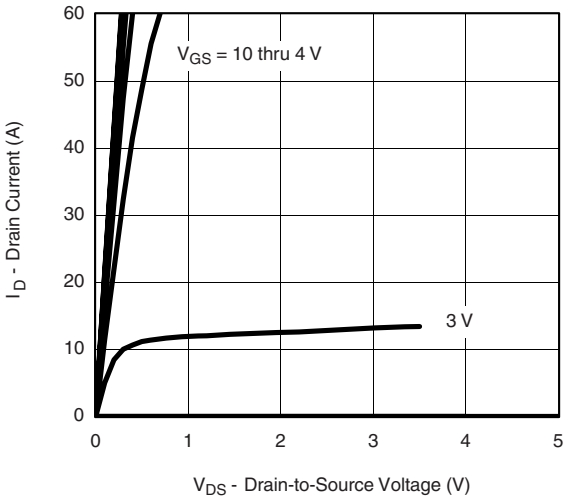
Notes:
a. Surface Mounted on 1" x 1" FR4 board.
b. See Solder Profile (*http://www.vishay.com/ppg?73257*). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components. .

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 µA	1.0		3.0	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			1	µA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 55 °C			5	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	30			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.0045	0.0055	Ω
		V_{GS} = 4.5 V, I_D = 16 A		0.0072	0.009	
Forward Transconductance[a]	g_{fs}	V_{DS} = 6 V, I_D = 20 A		48		S
Diode Forward Voltage[a]	V_{SD}	I_S = 4.5 A, V_{GS} = 0 V		0.76	1.1	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 20 A		16	25	nC
Gate-Source Charge	Q_{gs}			6		
Gate-Drain Charge	Q_{gd}			5.2		
Gate Resistance	R_g			1.8		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 10 Ω $I_D \cong$ 1 A, V_{GEN} = 10 V, R_G = 6 Ω		21	32	ns
Rise Time	t_r			16	25	
Turn-Off Delay Time	$t_{d(off)}$			58	90	
Fall Time	t_f			15	23	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 4.1 A, di/dt = 100 A/µs		40	80	

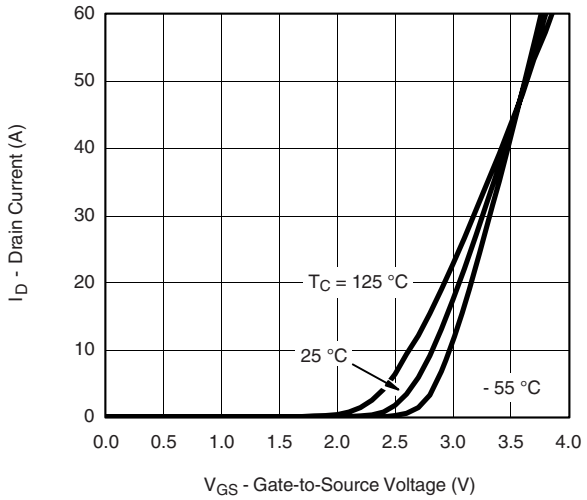
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

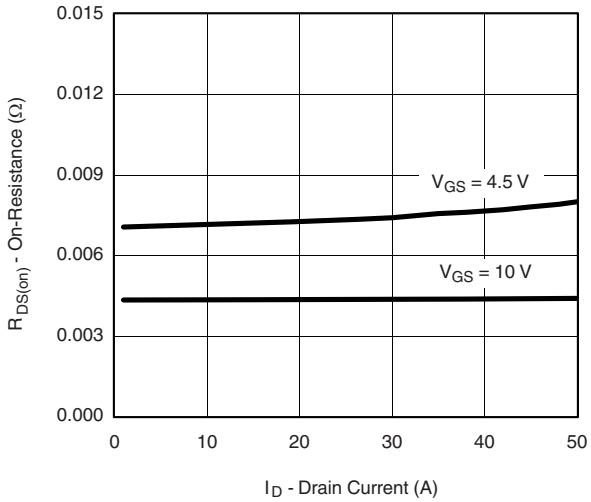


Output Characteristics

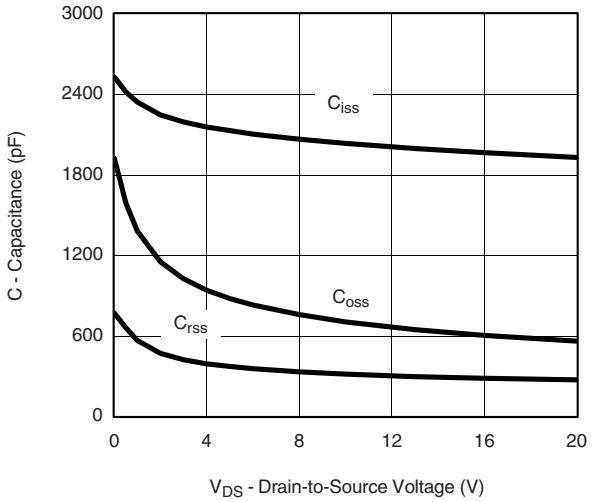


Transfer Characteristics

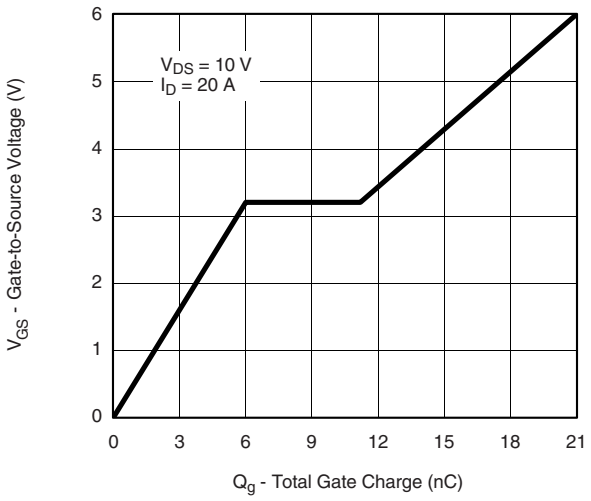
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



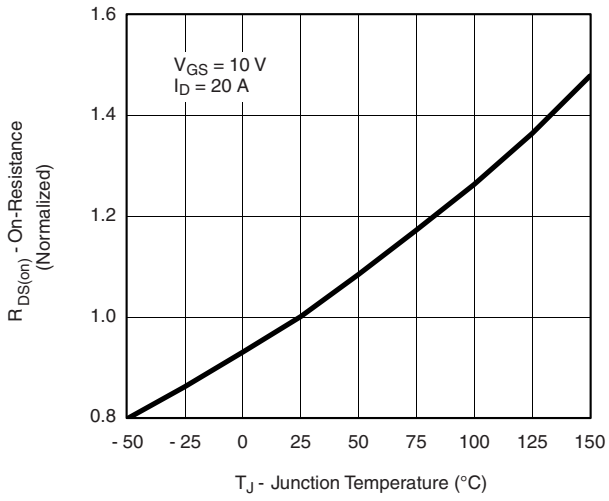
On-Resistance vs. Drain Current



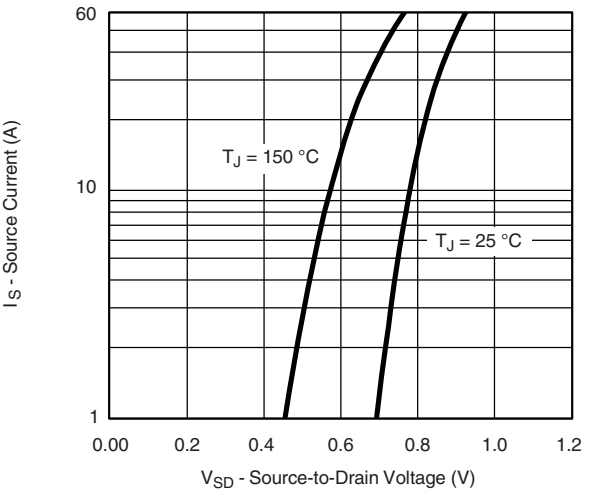
Capacitance



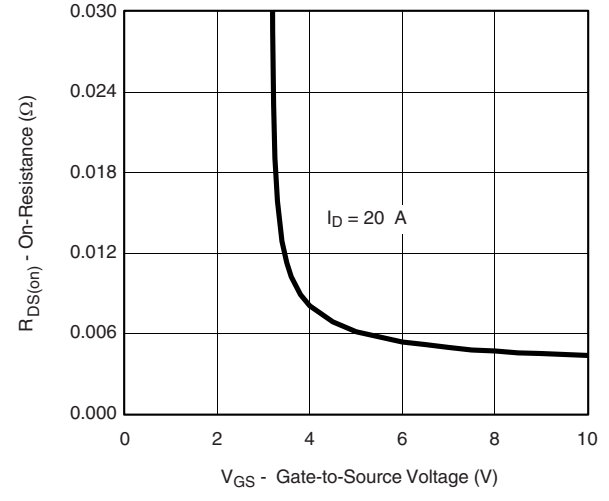
Gate Charge



On-Resistance vs. Junction Temperature

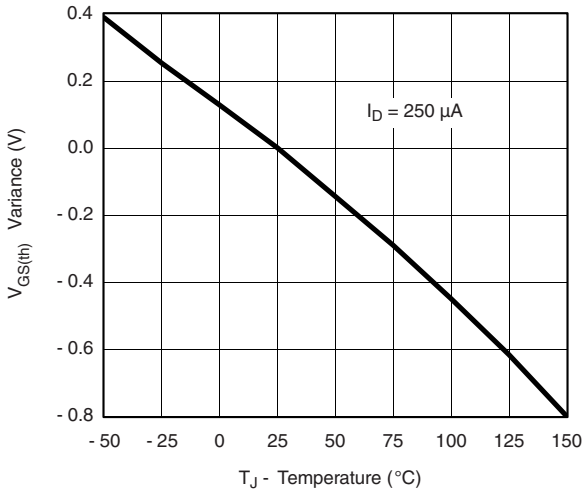


Source-Drain Diode Forward Voltage

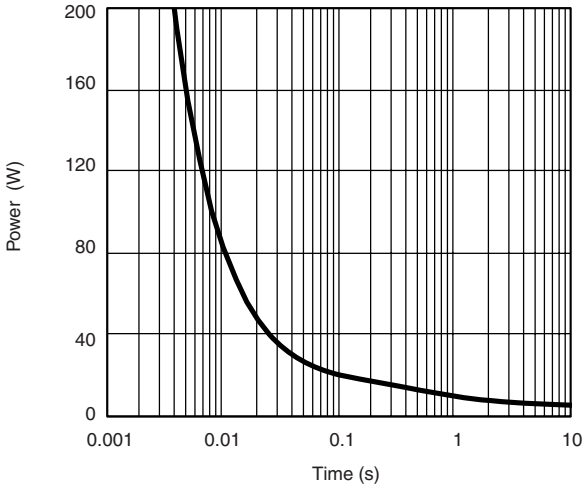


On-Resistance vs. Gate-to-Source Voltage

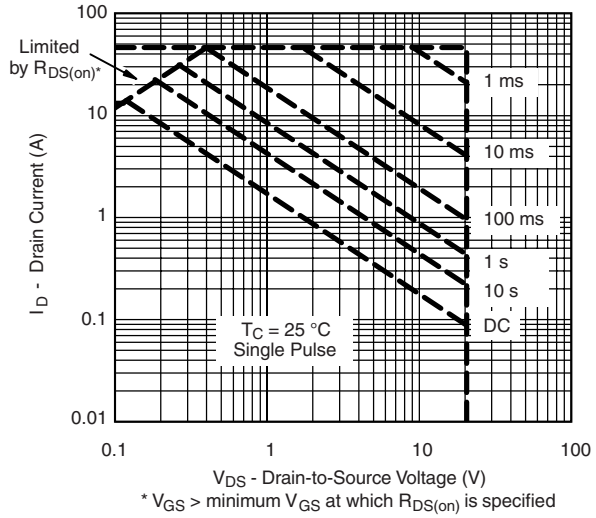
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



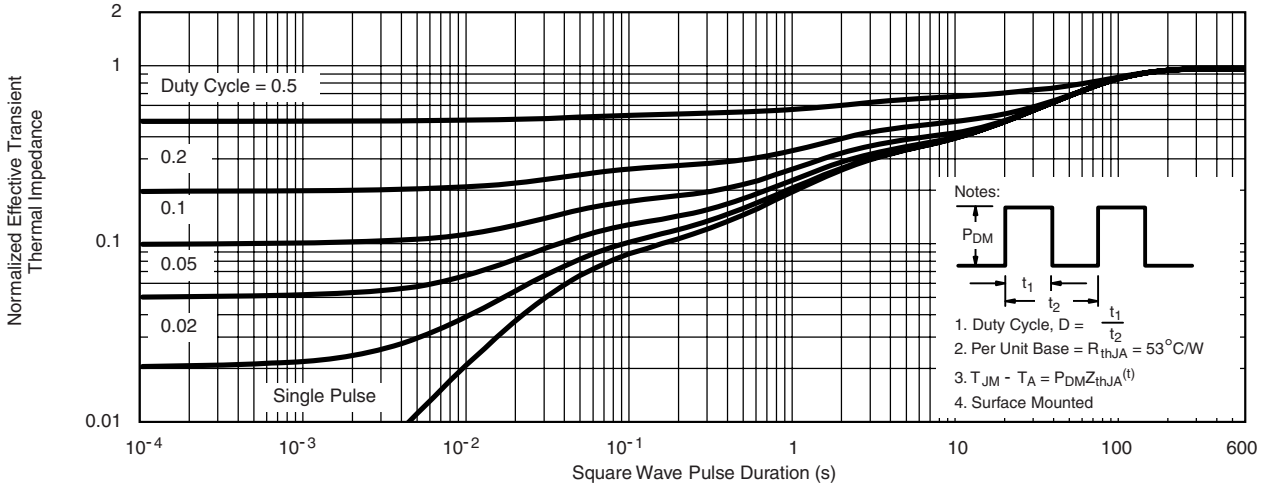
Threshold Voltage



Single Pulse Power

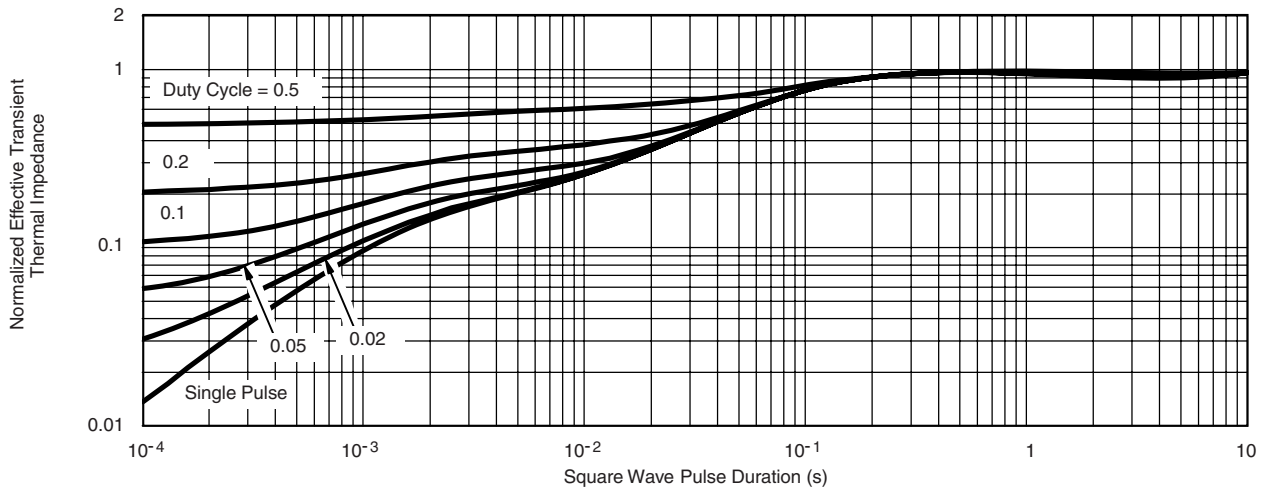


Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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